

ABSTRACT

A method for producing a compound semiconductor wafer used for production of HBT by vapor growth of a sub-collector layer, a collector layer, a base layer and an emitter layer in this turn on a compound semiconductor substrate using MOCVD method wherein the base layer is grown as a p-type compound semiconductor thin film layer containing at least one of Ga, Al and In as a Group III element and As as a Group V element under such growth conditions that the growth rate gives a growth determined by a Group V gas flow rate-feed.